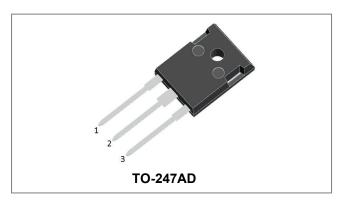


30CPQ200

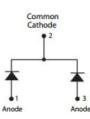
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30CPQ200 SCHOTTKY RECTIFIER



Circuit Diagram



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Center tap configuration

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	200	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @Tc=95°C, rectangular wave form	15(Per Leg) 30(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	408	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 15A, Pulse, T _J = 25 °C	0.85	1.05	V
	V _{F2}	@ 15A, Pulse, T _J = 125 °C	0.70	0.83	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R T _J = 25 °C	0.0001	0.1	mA
	I _{R2}	@V _R = rated V _R T _J = 125 °C	0.1	15	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	260	300	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

* Pulse width < 300 $\mu s, \ duty \ cycle < 2\%$

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com -

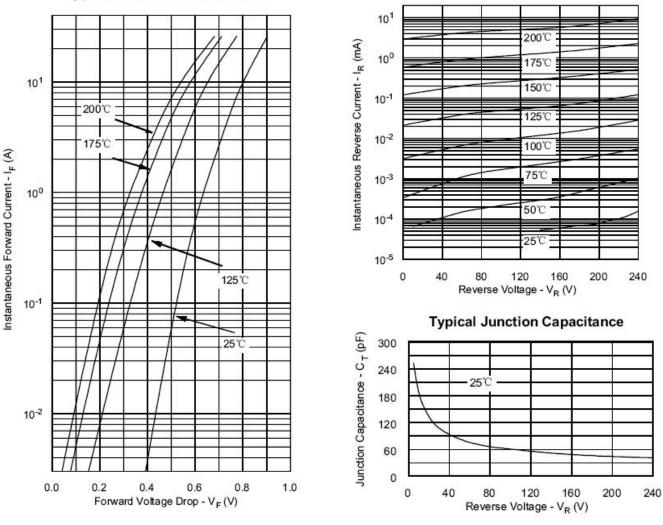


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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(per leg)	R _{0JC}	DC operation	1.1	°C/W
Typical Thermal Resistance, case to Heat Sink	R _{θcs}	Mounting surface, smooth and greased	0.24	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves



Typical Forward Characteristics

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Typical Reverse Characteristics

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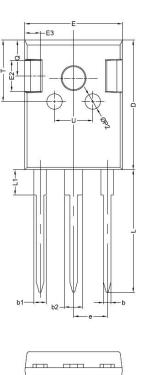


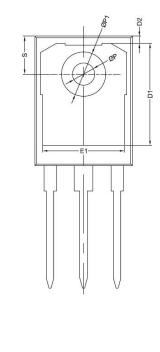
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30CPQ200

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Mechanical Dimensions TO-247AD





CYMDOL	Millimeters					
SYMBOL	MIN.	TYP.	MAX.			
А	4.80	5.00	5.20			
A1	2.20	2.41	2.61			
A2	1.90	2.00	2.10			
b	1.10	1.20	1.40			
b1	1.80	2.00	2.20			
b2	2.80	3.00	3.20			
С	0.50	0.60	0.75			
D	20.30	21.00	21.20			
D1		16.55				
D2		1.20				
E	15.45	15.80	16.00			
E1		13.30				
E2		5.00				
E3		2.50				
е		5.44				
L	19.42	19.92	20.70			
L1		4.13				
Р	3.50	3.60	3.70			
P1	7.1		7.40			
P2		2.50				
Q		5.80				
S T	6.05	6.15	6.25			
Τ		10.00				
U		6.20				

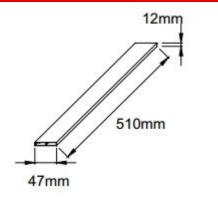
Ordering Information:

A1-

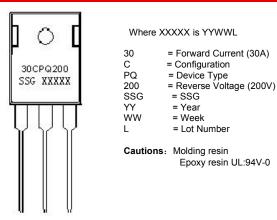
Device	Package	Shipping	
30CPQ200	TO-247AD(Pb-Free)	25pcs / tube	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification



Marking Diagram



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